



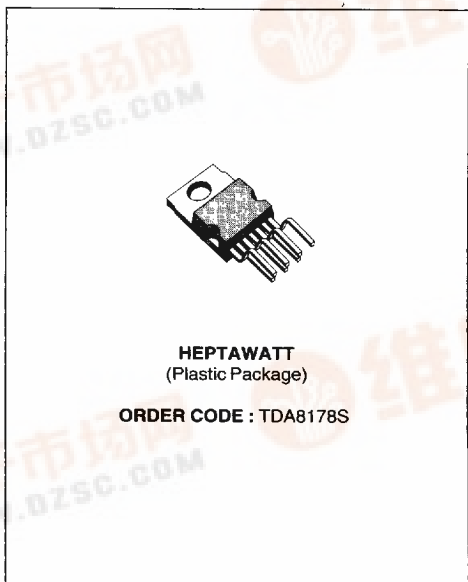
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TDA8178S

TV VERTICAL DEFLECTION BOOSTER

- POWER AMPLIFIER
- FLYBACK GENERATOR
- THERMAL PROTECTION
- REFERENCE VOLTAGE



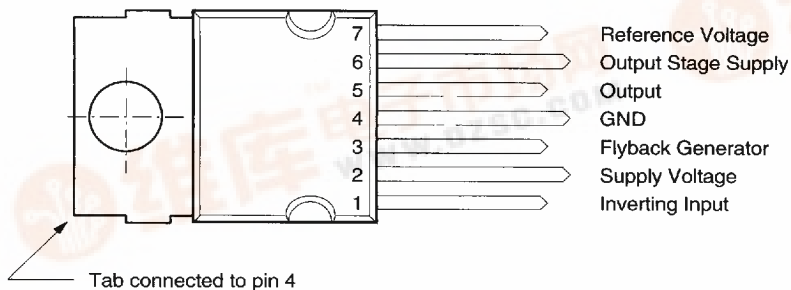
DESCRIPTION

Designed for monitors and high performance TVs, the TDA8178S vertical deflection booster delivers flyback voltages up to 90V.

The TDA8178S operates with supplies up to 42V and provides up to 2App output current to drive to yoke.

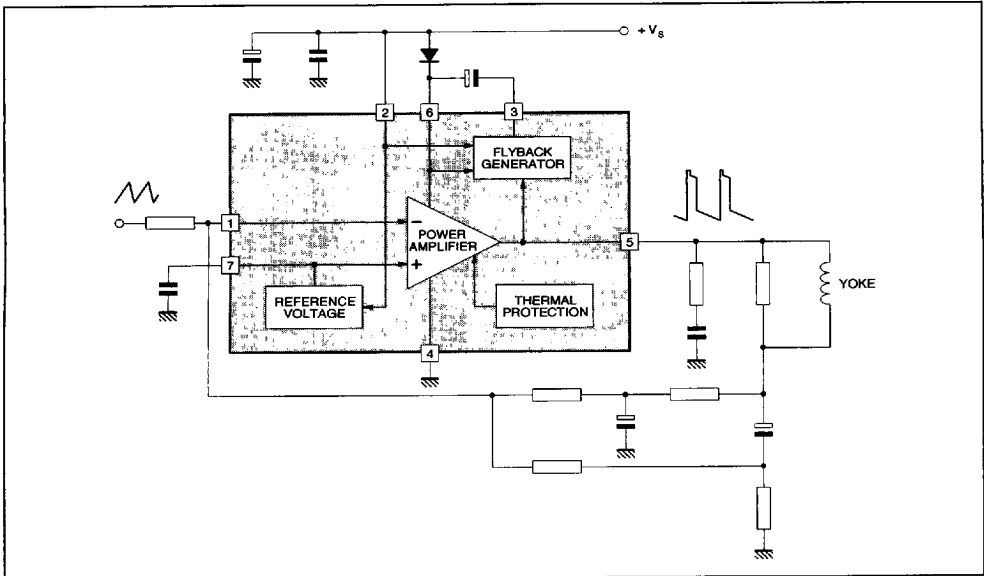
The TDA8178S is offered in HEPTAWATT package

PIN CONNECTIONS

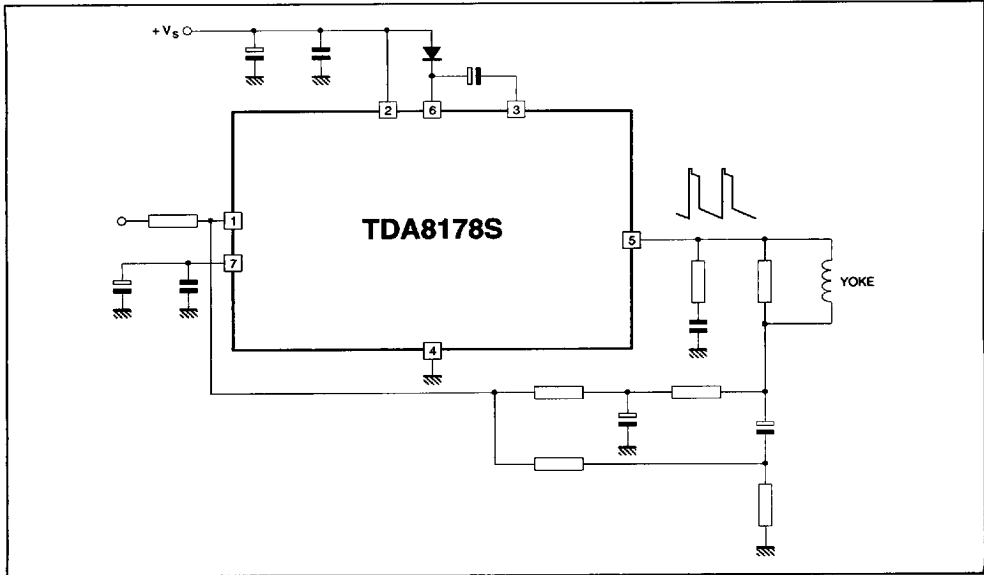


TDA8178S

BLOCK DIAGRAM



APPLICATION CIRCUIT ($V_S = 42V$)



Note : For values see "Easy Design of Vertical Deflection Stages" (software available from our sales offices)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_S	Supply Voltage (pin 2)	50	V
V_5, V_6	Flyback Peak Voltage	100	V
V_1, V_7	Amplifier Input Voltage	+ V_S	
I_O	Output Peak Current	2 2 1.8	A
	Non-repetitive, $t = 2\text{ms}$ $f = 50$ or 60Hz , $t \leq 10\mu\text{s}$ $f = 50$ or 60Hz , $t > 10\mu\text{s}$		
I_3	Pin 3 DC at $V_5 < V_2$ Pin 3 Peak Flyback Current at $f = 50$ or 60Hz , $t_{fly} \leq 1.5\text{ms}$	100 1.8	mA A
P_{tot}	Total Power Dissipation at $T_C = 70^\circ\text{C}$	20	W
T_{stg}	Storage Temperature	- 40, + 150	$^\circ\text{C}$
T_J	Junction Temperature	0, +150	$^\circ\text{C}$

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THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction-case Thermal Resistance	Max. 3	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

(V_S = 42V, T_A = 25°C, unless otherwise specified) (refer to the test circuits - see Figure 1 next page)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_S	Operating Supply Voltage Range		10		42	V
I_2	Pin 2 Quiescent Current	$I_3 = 0$ $I_5 = 0$		10	20	mA
I_6	Pin 6 Quiescent Current	$I_3 = 0$ $I_5 = 0$		20	40	mA
I_1	Amplifier Bias Current	$V_1 = 1\text{V}$		- 0.2	- 1	μA
V_{3L}	Pin 3 Saturation to GND	$I_3 = 20\text{mA}$		1.3	1.8	V
V_5	Quiescent Output Voltage	$V_S = 42\text{V}$ $R_A = 3.9\text{k}\Omega$ $V_S = 35\text{V}$ $R_A = 5.6\text{k}\Omega$	23.4 17	24.2 17.8	25 18.5	V
V_{5L}	Output Saturation Voltage to GND	$I_5 = 1\text{A}$		1.2	1.5	V
V_{5H}	Output Saturation Voltage to Supply	- $I_5 = 1\text{A}$		2.2	2.6	V
V_{D5-6}	Diode Forward Voltage between Pins 5-6	$I_D = 1\text{A}$		1.5	3	V
V_{D3-2}	Diode Forward Voltage between Pins 3-2	$I_D = 1\text{A}$		1.5	3	V
V_7	Internal Reference		2.1	2.2	2.3	V
$\Delta V_7 / \Delta V_S$	Reference Voltage Drift versus V_S	$V_S = 24$ to 42V		2	4	mV/V
K_T	Reference Voltage Drift versus T_J	$T_J = 0$ to 125°C $K_T = \frac{\Delta V_7 \cdot 10^6}{\Delta T_J \cdot V_7}$		100	150	ppm/ $^\circ\text{C}$
R_1	Input Resistance			200		k Ω
T_J	Junction Temperature for Thermal Shutdown			140		$^\circ\text{C}$

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FIGURE 1 : DC Test Circuits

Figure 1a : Measurement of I_1 , I_2 , I_6 , V_7 , $\Delta V_7/\Delta V_S$

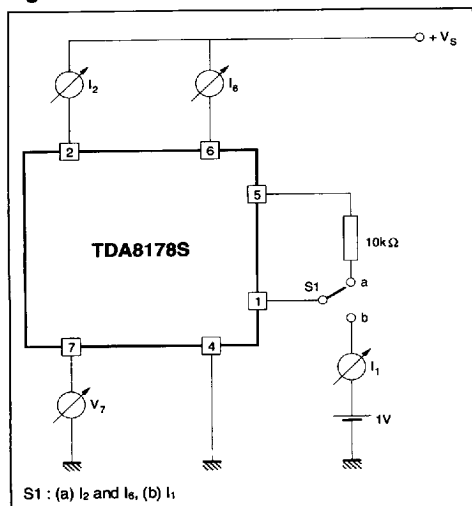


Figure 1b : Measurement of V_{SH}

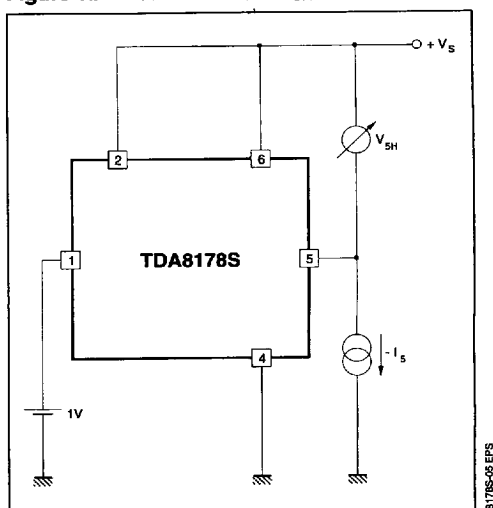


Figure 1c : Measurement of V_{3L} , V_{5L}

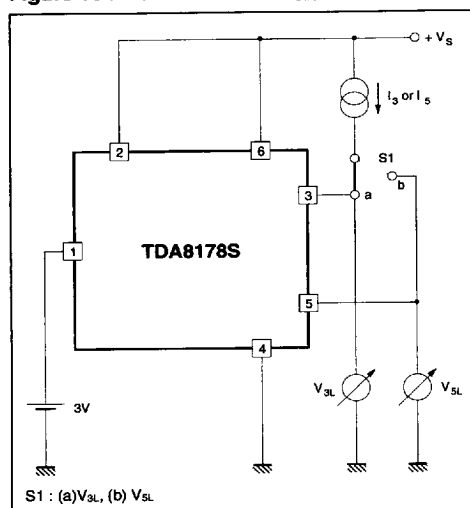


Figure 1d : Measurement of V_S

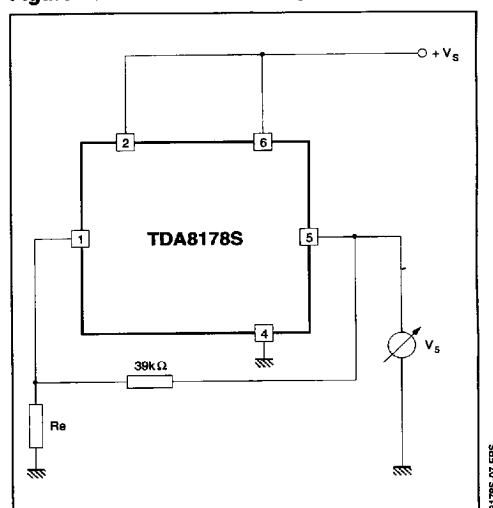


Figure 2 : SOA of Each Output Power Transistor at $T_A = 25^\circ\text{C}$ 